



Silicon Wafer Japan TC Chapter

In conjunction with SEMICON Japan 2024

Thursday, December 12, 2024

Room 701, Int'l Conference Tower, Tokyo Big Sight, Tokyo, Japan/ Official Virtual TC Chapter Meeting (Hybrid)

9:00 AM — 12:00 PM JST

AGENDA

1 Welcome/Call to Order

- 1.1 Introductions
- 1.2 Required Elements (Membership Requirements, Antitrust and Intellectual Property Reminders, and Effective Meeting Guidelines)
- 1.3 Agenda Review

2 Review of Previous Meeting Minutes

3 Liaison Report

- 3.1 Japan Regional Standards Committee (JRSC)
- 3.2 Global Coordinating Subcommittee (GCS)
- 3.3 Europe TC Chapter
- 3.4 North America TC Chapter

4 Staff Report

5 Ballot Review

- 5.1 Doc.#7265, Reapproval of SEMI MF391-0310E, Test Method for Minority Carrier Diffusion Length in Extrinsic Semiconductors by Measurement of Steady-State Surface Photovoltage
- 5.2 Doc.#7266, Reapproval of SEMI M71-0120, Specification for Silicon-on-Insulator (SOI) Wafers for CMOS LSI
- 5.3 Doc.#7291, Revision to SEMI M62-0317, Specification For Silicon Epitaxial Wafers

6 Subcommittee & Task Force Reports

- 6.1 International Advanced Wafer Geometry Task Force
- 6.2 International/ Japan Test Method Task Force

- 6.3 International Advanced Surface Inspection Task Force
- 6.4 International Polished Wafers Task Force
- 6.5 International Epitaxial Wafers Task Force
- 6.6 International Annealed Wafers Task Force
- 6.7 International SOI Wafers Task Force
- 6.8 International Terminology Task Force

7 Old Business

7.1 Project Period Review

- SNARF 6570, New Standard: Guide for Measuring Bulk Micro Defect Density and Denuded Zone Width in Annealed Silicon Wafers by a Laser-Scattering Tomography Technique
- SNARF 6687, Revision of M51, Test Method for Characterizing Silicon Wafer by Gate Oxide Integrity
- SNARF 6702, Revision of M60, Test Method for Time Dependent Dielectric Breakdown Characteristics of Amorphous SiO₂ Films for Silicon Wafer Evaluation

7.2 5-year Review

- SEMI M85-0120, Guide for the Measurement of Trace Metal Contamination on Silicon Wafer Surface by Inductively Coupled Plasma Mass Spectrometry
- SEMI M88-0119, Practice for Sample Preparation Methods for Measuring Minority Carrier Diffusion Length in Silicon Wafers by Surface Photovoltage Methods

8 New Business

- 8.1 SNARF for New Standard: Test Method for Net Carrier Density and Resistivity of Silicon Epitaxial Layer by Capacitance-Voltage Measurements with an Evaporated Metal Schottky Diode
- 8.2 SNARF for Revision to SEMI M1-0924, Specification for Polished Single Crystal Silicon Wafers

9 Action Item Review

9.1 Open Action Items

<i>Item #</i>	<i>Assigned to</i>	<i>Details</i>
SW20240829-01	SEMI Staff	To have a training session of Connect@SEMI for TF leaders.
SW20240829-02	Hitoshi Tsunoda (Shin-Etsu Handotai)	To submit SEMI M62 Revision Ballot (Doc.#7291) for Cycle 8 on the condition that SEMI M73 reference to the edge profile be included in the table of M62.
SW20240829-03	Tetsuya Nakai (SUMCO)	To confirm the EU AWG TF leader whether the draft of SEMI M73 Revision ballot (Doc.#7192) was distributed to all the TF members for their inputs at least one week before submission to SEMI staff.

9.2 New Action Items

<i>Item #</i>	<i>Assigned to</i>	<i>Details</i>

10 Next Meeting and Adjournment

10.1 The next meeting is scheduled for <date> at <event/location>.